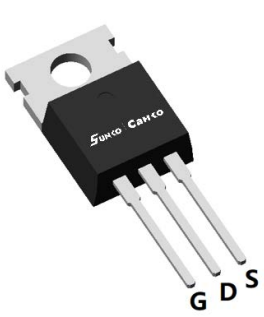
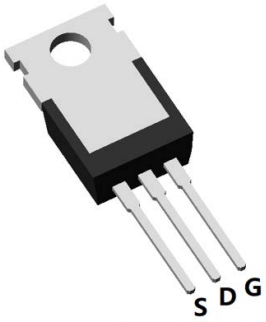
SCP270G10H

N-Channel Enhancement Mode Field Effect Transistor

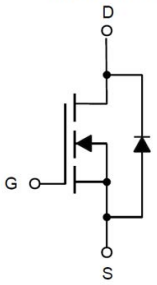


Top View



Bottom View

TO-220



Product Summary

- V_{DS} 100V
- I_D 270A
- $R_{DS(ON)}$(at V_{GS}=10V) ＜2.6mΩ
- $R_{DS(ON)}$(at V_{GS}=6V) ＜3.1mΩ
- 100% EAS Tested
- 100% ▽V_{DS} Tested

General Description

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Load switch
- Battery management
- Solar

■ Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	100	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_A=25℃	I_D	27	A
	T_A=100℃		19	
	T_C=25℃		270	
	T_C =100℃		190	
Pulsed Drain Current [A]		I_{DM}	1080	A
Avalanche energy [B]		EAS	1440	mJ
Total Power Dissipation [C]	T_A=25℃	P_D	4.2	W
	T_A=100℃		2.1	
	T_C=25℃		300	
	T_C =100℃		150	
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+175	℃

■Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient [D]	Steady-State	$R_{\theta JA}$	27	35	℃/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.4	0.5	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SCP270G10H	B1	SCP270G10H	50	/	5000	Tube

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250uA	100	-	-	V
		V_{GS}= 0V, I_D=10mA	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V	-	-	1	μA
		V_{DS}=100V, V_{GS}=0V, Tj=125℃	-	-	100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	2	2.6	4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=50A	-	1.95	2.6	mΩ
		V_{GS}=10V, I_D=20A	-	1.95	2.6	
		V_{GS}=6V, I_D=20A	-	2.35	3.1	
Diode Forward Voltage	V_{SD}	I_S=50A, V_{GS}=0V	-	-	1.2	V
Gate resistance	R_G	f=1MHz	-	1.3	-	Ω
Maximum Body-Diode Continuous Current	I_S		-	-	270	A
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=50V, V_{GS}=0V, f=1MHz	-	10700	-	pF
Output Capacitance	C_{oss}		-	2125	-	
Reverse Transfer Capacitance	C_{rss}		-	31	-	
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V, V_{DS}=50V, I_D=30A	-	166	-	nC
Gate-Source Charge	Q_{gs}		-	34	-	
Gate-Drain Charge	Q_{gd}		-	49	-	
Reverse Recovery Charge	Q_{rr}	I_F=30A, di/dt=100A/us	-	167	-	nC
Reverse Recovery Time	t_{rr}		-	92	-	ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V, V_{DD}=50V, I_D=30A R_{GEN}=4.5Ω	-	30	-	ns
Turn-on Rise Time	t_r		-	65	-	
Turn-off Delay Time	$t_{D(off)}$		-	121	-	
Turn-off fall Time	t_f		-	107	-	

A. Repetitive rating; pulse width limited by max. junction temperature.
B. T_J=25℃, V_G=10V, R_G=25Ω, L=5mH, IAS=24A.
C. P_d is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.
D. The value of $R_{\theta JA}$ is measured with the device mounted on the 40mm*40mm*1.1mm FR-4 PCB board with 1 in^2 pad of 2oz. Copper, in the still air environment with TA =25℃.The maximum allowed junction temperature of 175℃. The value in any given application depends on the user's specific board design.

■Typical Electrical and Thermal Characteristics Diagrams

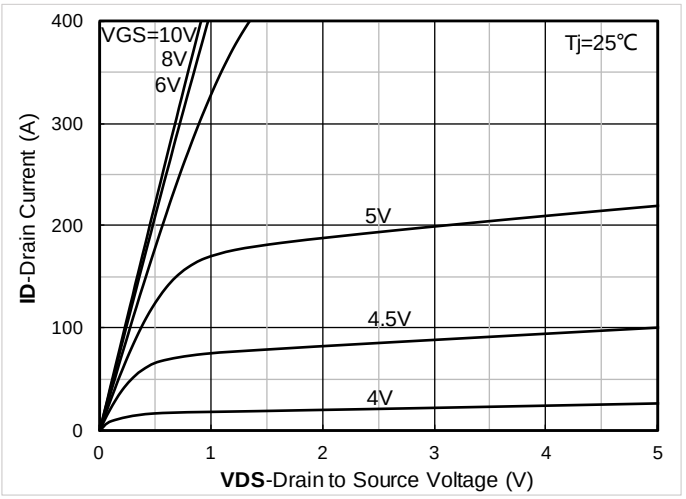


Figure 1. Output Characteristics

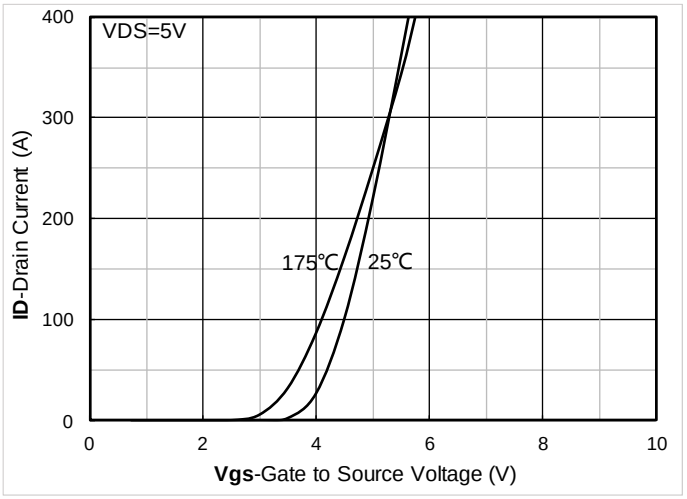


Figure 2. Transfer Characteristics

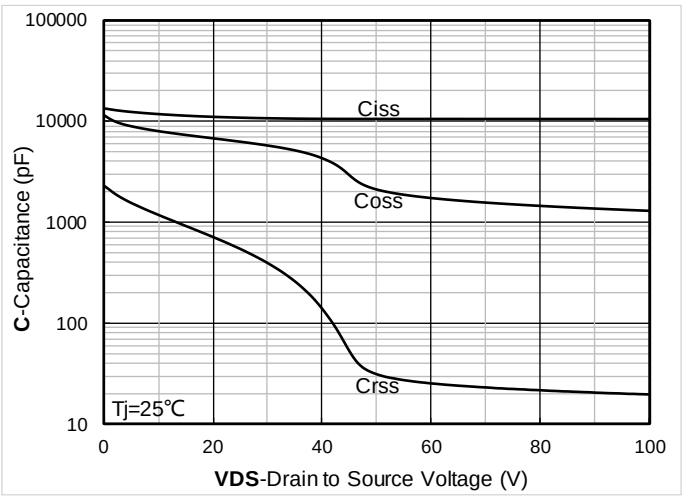


Figure 3. Capacitance Characteristics

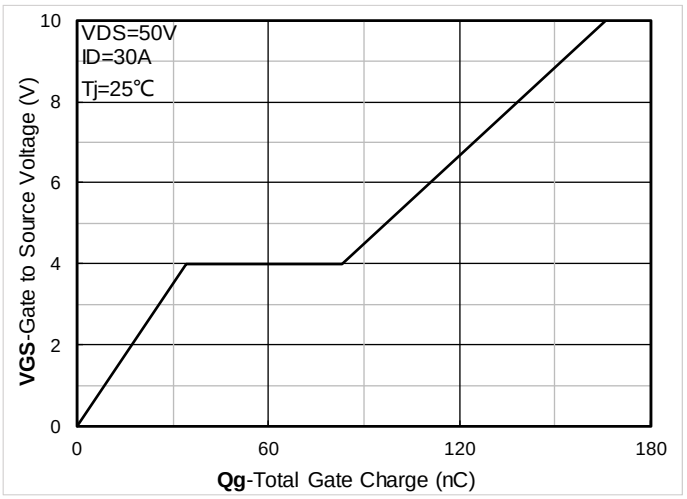


Figure 4. Gate Charge

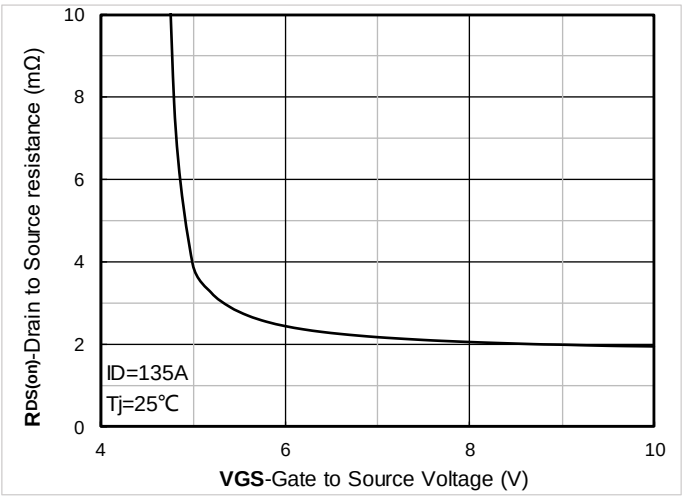


Figure 5. On-Resistance vs Gate to Source Voltage

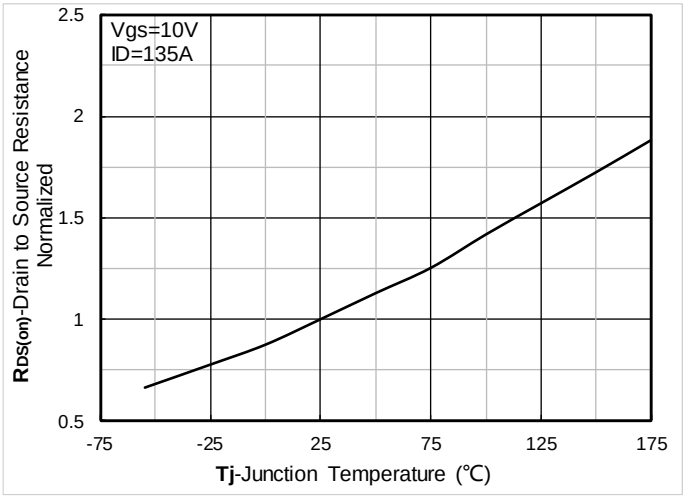


Figure 6. Normalized On-Resistance

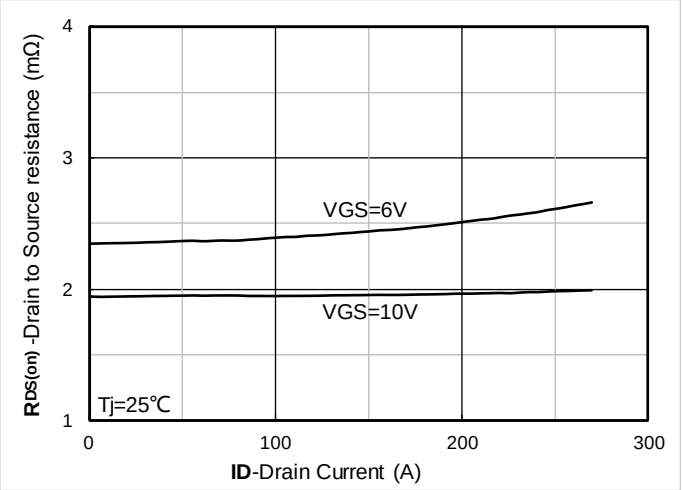


Figure 7. $R_{DS(on)}$ VS Drain Current

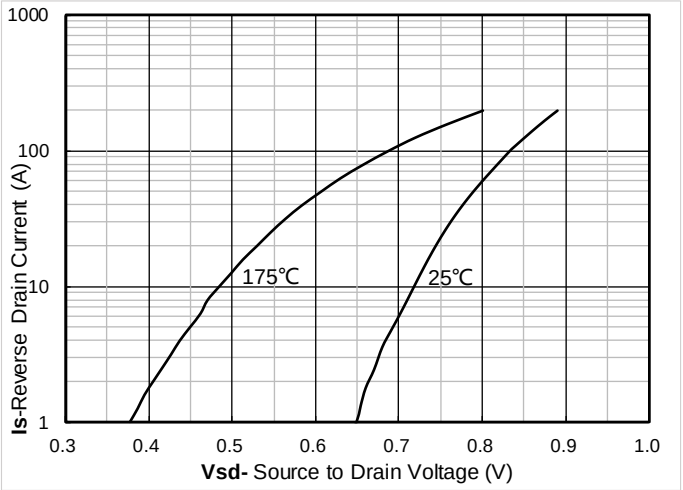


Figure 8. Forward characteristics of reverse diode

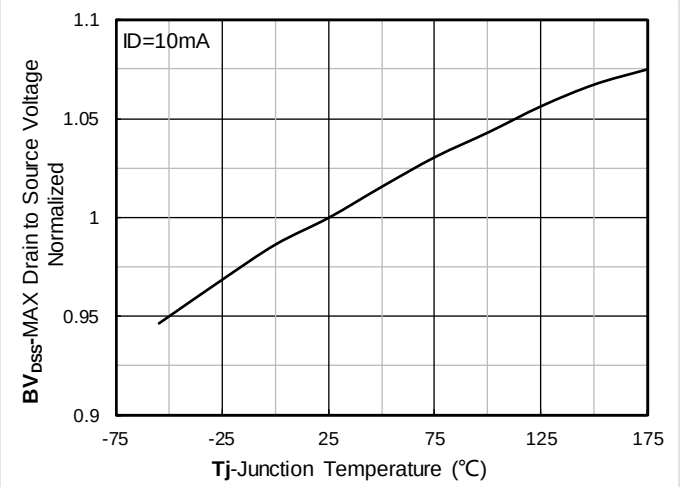


Figure 9. Normalized breakdown voltage

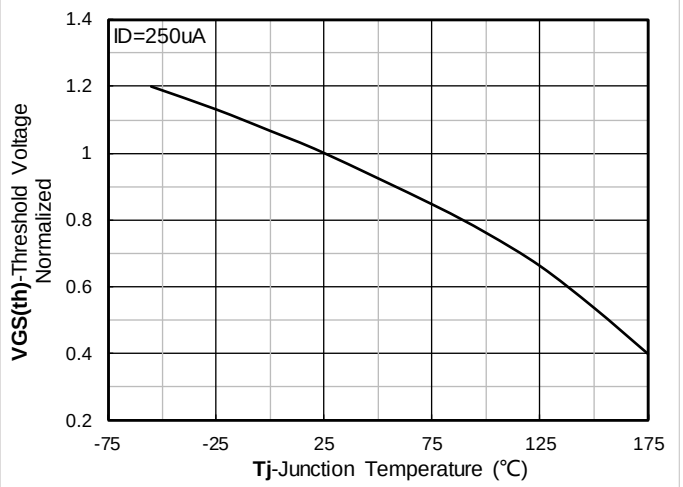


Figure 10. Normalized Threshold voltage

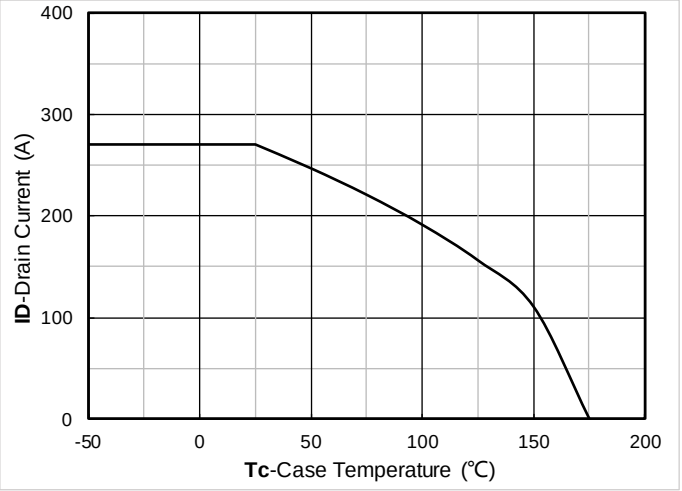


Figure 11. Current dissipation

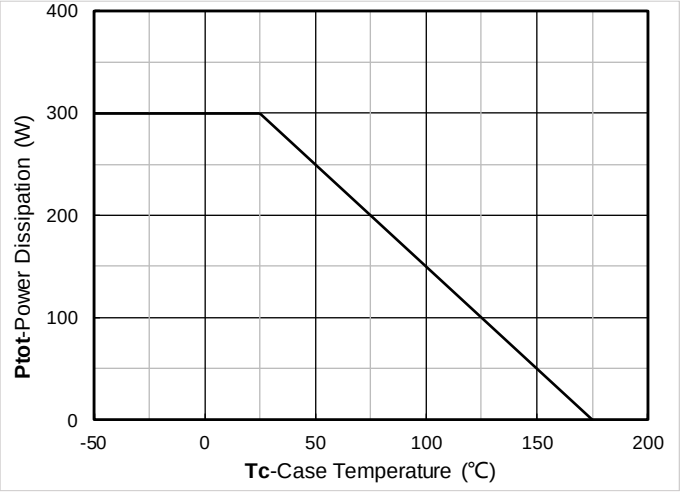


Figure 12. Power dissipation

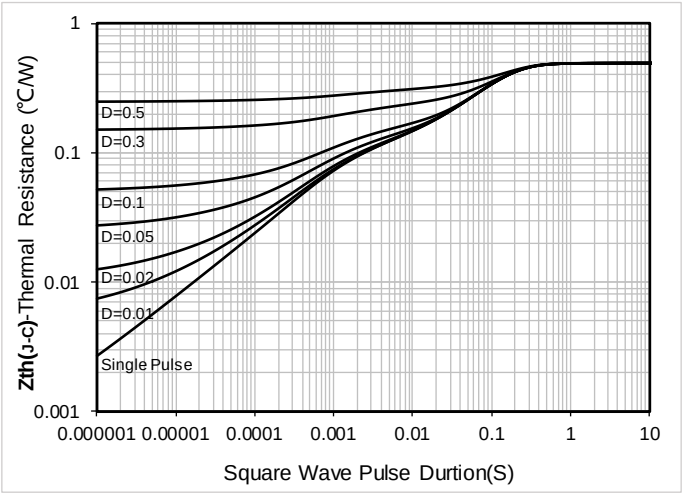


Figure 13. Maximum Transient Thermal Impedance

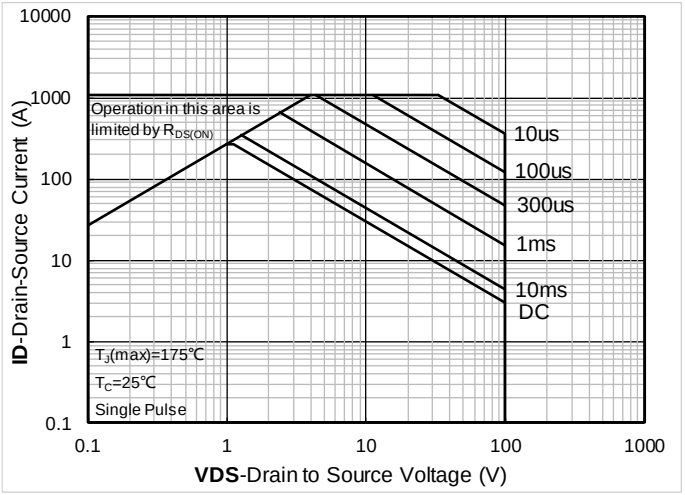


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

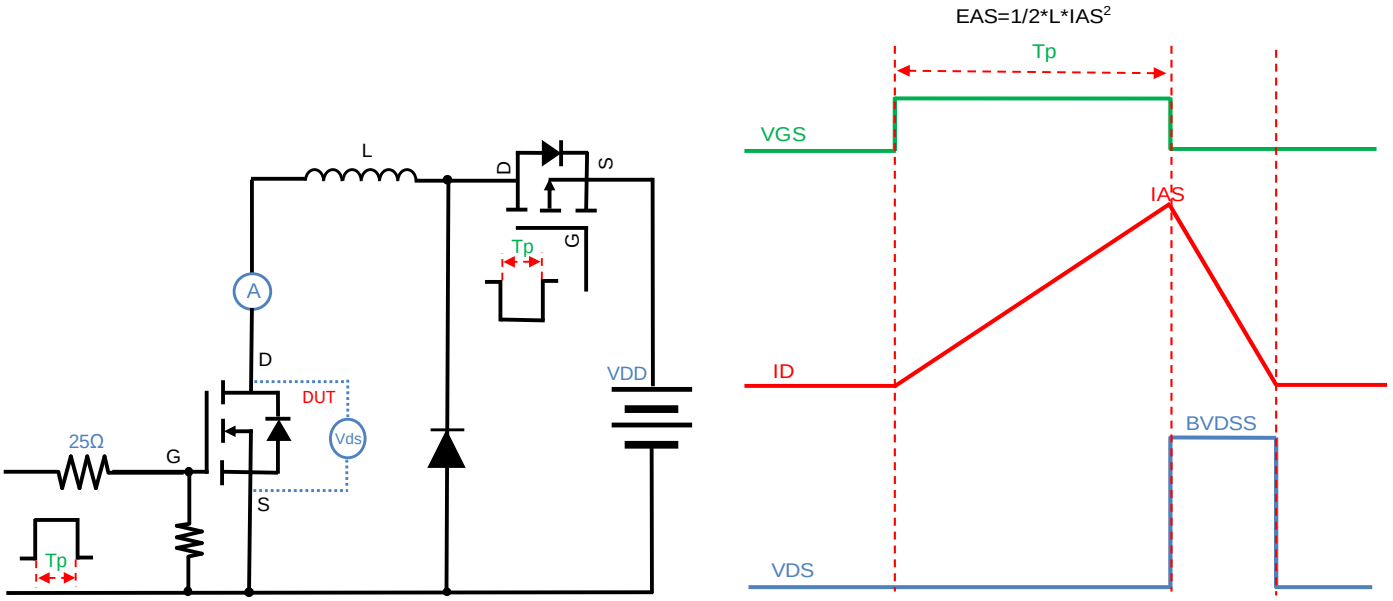


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

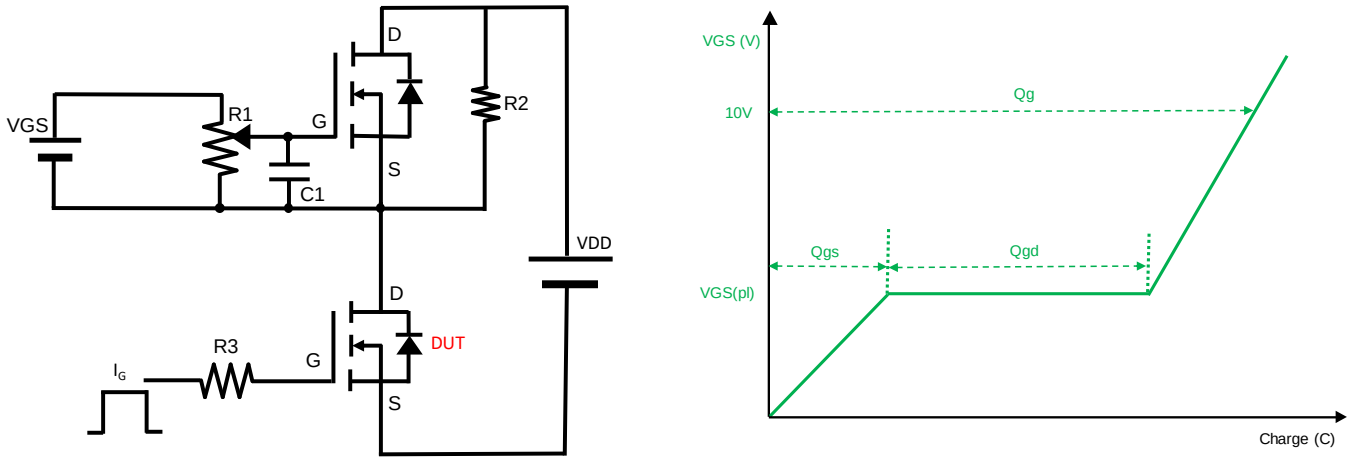


Figure B. Gate Charge Test Circuit & Waveform

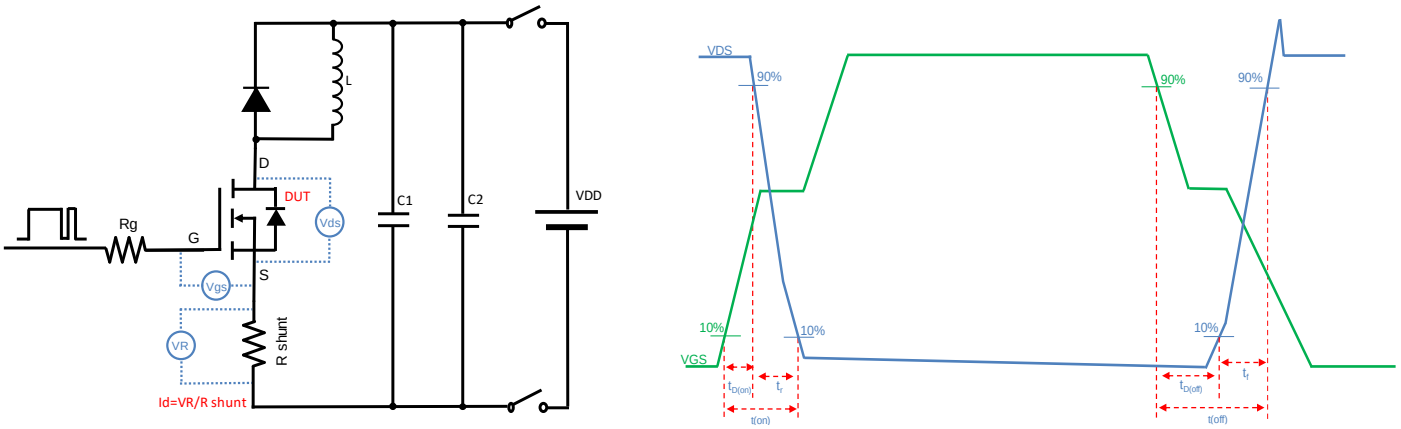


Figure C. Resistive Switching Test Circuit & Waveform

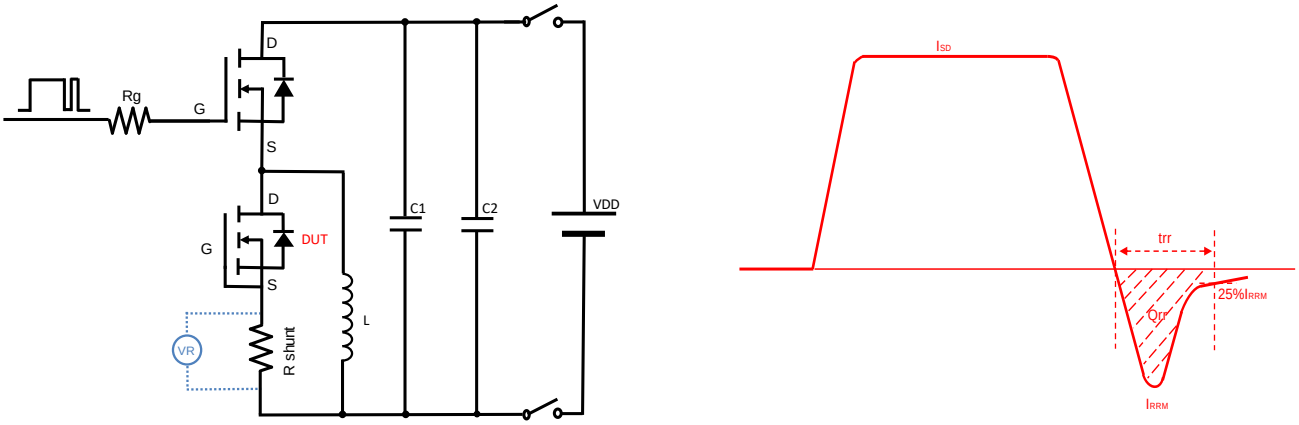
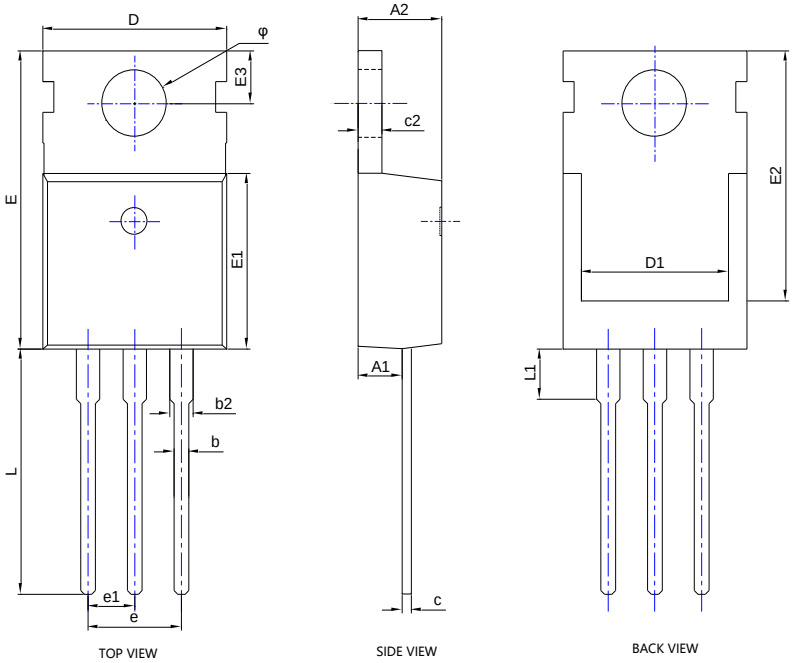


Figure D. Diode Recovery Test Circuit & Waveform

■ TO-220AB-E Package information



DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A1	0.093	0.114	2.350	2.900
A2	0.176	0.184	4.470	4.670
b	0.028	0.036	0.710	0.910
b2	0.048	0.054	1.220	1.360
c	0.019	0.024	0.470	0.600
c2	0.047	0.055	1.200	1.400
D	0.382	0.408	9.700	10.370
D1	0.276	0.350	7.000	8.890
E	0.579	0.622	14.700	15.800
E1	0.350	0.373	8.900	9.470
E2	0.463	0.535	11.750	13.600
E3	0.108BSC		2.740BSC	
e	0.200BSC		5.080BSC	
e1	0.100BSC		2.540BSC	
L	0.508	0.583	12.900	14.800
L1	0.100	0.151	2.540	3.840
φ	0.142	0.154	3.600	3.900

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.

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